

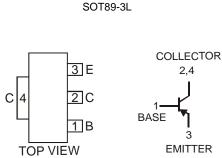


2DB1132P/Q

PNP SURFACE MOUNT TRANSIS

Features

- **Epitaxial Planar Die Construction**
- Complementary NPN Type Available (2DD1664)
- Ideally Suited for Automated Assembly Processes
- Ideal for Medium Power Switching or Amplification Applications
- Lead Free By Design/RoHS Compliant (Note 1)
- "Green" Device (Note 2)
- **Mechanical Data**
 - Case: SOT89-3L
 - Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
 - Moisture Sensitivity: Level 1 per J-STD-020C
 - Terminals: Finish Matte Tin annealed over Copper leadframe (Lead Free Plating). Solderable per MIL-STD-202, Method 208
 - Marking & Type Code Information: See Page 3
 - Ordering Information: See Page 3
 - Weight: 0.072 grams (approximate)



Schematic and Pin Configuration

Maximum Ratings @T_A = 25°C unless otherwise specified

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V _{CBO}	-40	V
Collector-Emitter Voltage	V _{CEO}	-32	V
Emitter-Base Voltage	V _{EBO}	-5	V
Peak Pulse Current	I _{CM}	-2	A
Continuous Collector Current	lc	-1	А

Thermal Characteristics

Characteristic	Symbol	Value	Unit
Power Dissipation (Note 3) @ $T_A = 25^{\circ}C$	PD	1	W
Thermal Resistance, Junction to Ambient Air (Note 3) @ $T_A = 25^{\circ}C$	$R_{ extsf{ heta}JA}$	125	°C/W
Operating and Storage Temperature Range	T _j , T _{STG}	-55 to +150	٥°C

Electrical Characteristics @T_A = 25°C unless otherwise specified

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Characteristic		Symbol	Min	Тур	Max	Unit	Conditions
OFF CHARACTERISTICS (Note 4)					-		
Collector-Base Breakdown Voltage		V _{(BR)CBO}	-40		_	V	$I_{C} = -50 \mu A, I_{E} = 0$
Collector-Emitter Breakdown Voltage		V _{(BR)CEO}	-32	_	_	V	$I_{\rm C} = -1 {\rm mA}, \ I_{\rm B} = 0$
Emitter-Base Breakdown Voltage		V _{(BR)EBO}	-5			V	$I_{E} = -50 \mu A, I_{C} = 0$
Collector Cut-Off Current		I _{CBO}	_	_	-0.5	μA	$V_{CB} = -20V, I_E = 0$
Emitter Cut-Off Current		I _{EBO}	_	—	-0.5	μA	$V_{EB} = -4V, I_{C} = 0$
ON CHARACTERISTICS (Note 4)							
Collector-Emitter Saturation Voltage		V _{CE(SAT)}	_	-0.125	-0.5	V	$I_{\rm C} = -500 {\rm mA}, I_{\rm B} = -50 {\rm mA}$
DC Current Gain	2DB1132P	ר ג h _{FE}	82	_	180	_	
	2DB1132Q		120	_	270		$V_{CE} = -3V$, $I_{C} = -100mA$
	2DB1132R		180	_	390		1
SMALL SIGNAL CHARACTERISTICS					-		
Transition Frequency		f _T		190		MHz	$V_{CE} = -5V$, $I_E = 50mA$ f = 30MHz
Output Capacitance		C _{ob}		12	30	pF	$V_{CB} = -10V, I_E = 0,$ f = 1MHz

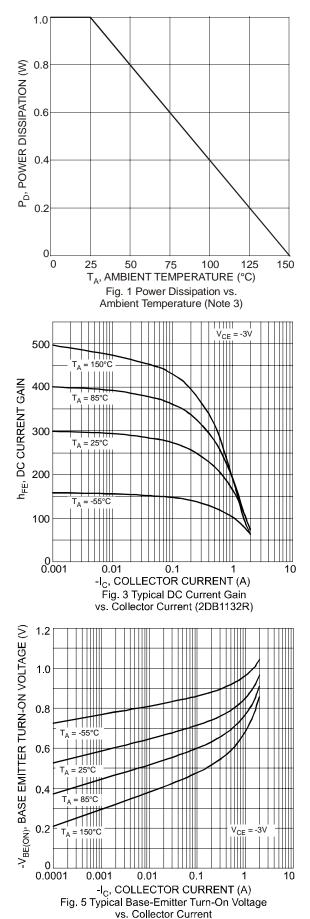
1. No purposefully added lead. Notes:

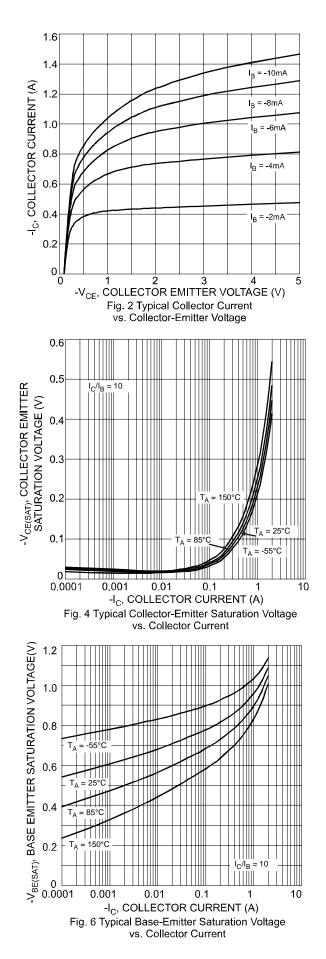
2.

Diodes Inc.'s "Green" policy can be found on our website at http://www.diodes.com/products/lead_free/index.php. Device mounted on FR-4 PCB; pad layout as shown on page 4 or in Diodes Inc. suggested pad layout document AP02001, which can be found on our 3. website at http://www.diodes.com/datasheets/ap02001.pdf.

4. Measured under pulsed conditions. Pulse width = 300μ s. Duty cycle $\leq 2\%$.

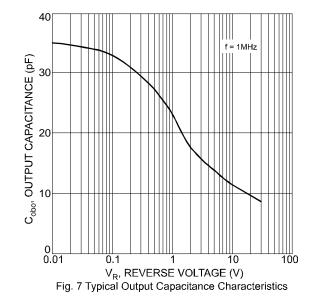


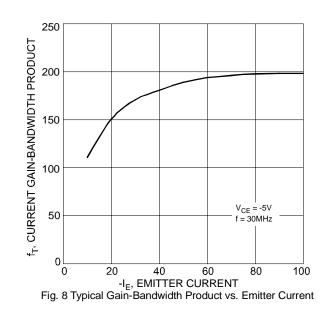




NEW PRODUCT





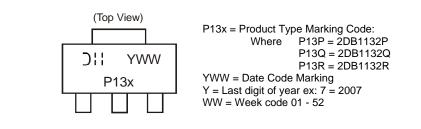


Ordering Information (Note 5)

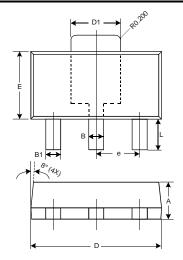
Device	Packaging	Shipping
2DB1132P-13	SOT89-3L	2500/Tape & Reel
2DB1132Q-13	SOT89-3L	2500/Tape & Reel
2DB1132R-13	SOT89-3L	2500/Tape & Reel

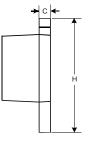
Notes: 5. For packaging details, please see below or go to our website at http://www.diodes.com/ap02007.pdf.

Marking Information



Package Outline Dimensions

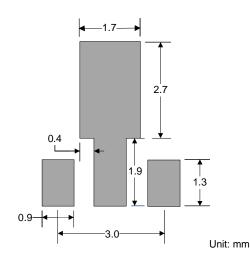




	SOT89-3L					
Dim	Min	Max	Тур			
Α	1.40	1.60	1.50			
В	0.45	0.55	0.50			
B1	0.37	0.47	0.42			
С	0.35	0.43	0.38			
D	4.40	4.60	4.50			
D1	1.50	1.70	1.60			
ш	2.40	2.60	2.50			
e		_	1.50			
н	3.95	4.25	4.10			
L	0.90	1.20	1.05			
All Dimensions in mm						



Suggested Pad Layout



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